

PATENT HAMME

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U.S. **UTILITY** Patent Application

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APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER	*
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Crystal growth method, crystal growth apparatus, group-III nitride crystal and group-III nitride semiconductor device

PTO-2040 12/99

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,	/ ISSUING CLASSIFICATION											
	ORIGINAL					CROSS REFERENCE(S)						
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Total Claims	Print Claim for O.G.	
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ISSUE FEE		
Amount Due	Date Paid	
ISSUE BA	TCH NUMBER	
	35, Sections 122, 181 and 368.	
2	e United States Code Title 3 actors only. H: DISK (CRF)	